

P-CHANNEL MOS FIELD EFFECT TRANSISTOR
FOR SWITCHING

DESCRIPTION

The 2SJ648 is a switching device which can be driven directly by a 2.5 V power source.

The 2SJ648 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 2.5 V drive available
- Low on-state resistance
 - $R_{DS(on)1} = 1.45 \Omega \text{ MAX.}$ ($V_{GS} = -4.5 \text{ V}$, $I_D = -0.2 \text{ A}$)
 - $R_{DS(on)2} = 1.55 \Omega \text{ MAX.}$ ($V_{GS} = -4.0 \text{ V}$, $I_D = -0.2 \text{ A}$)
 - $R_{DS(on)3} = 2.98 \Omega \text{ MAX.}$ ($V_{GS} = -2.5 \text{ V}$, $I_D = -0.15 \text{ A}$)

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ648	SC-75 (USM)

Marking: H1

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	-20	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	∓ 12	V
Drain Current (DC)	$I_{D(DC)}$	∓ 0.4	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	∓ 1.6	A
Total Power Dissipation ^{Note2}	P_T	200	mW
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

- Notes**
1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$
 2. Mounted on ceramic substrate of $300 \text{ mm}^2 \times 0.64 \text{ mm}$.

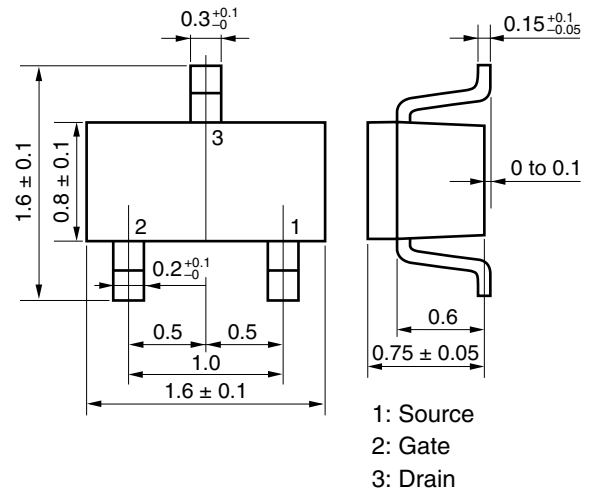
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

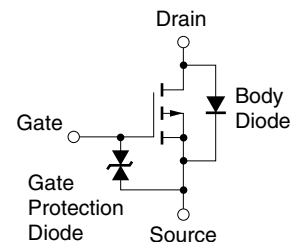
$V_{ESD} = \pm 100 \text{ V TYP.}$ ($C = 200 \text{ pF}$, $R = 0 \Omega$, Single pulse)

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★ PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT

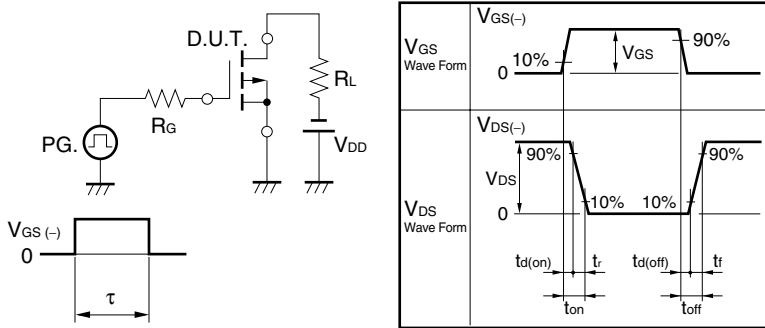


ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1.0	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \mp 12\text{ V}, V_{DS} = 0\text{ V}$			∓ 10	μA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{ V}, I_D = -1.0\text{ mA}$	-0.8	-1.3	-1.8	V
Forward Transfer Admittance ^{Note}	$ y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -0.2\text{ A}$	0.2	0.6		S
Drain to Source On-state Resistance ^{Note}	$R_{DS(on)1}$	$V_{GS} = -4.5\text{ V}, I_D = -0.2\text{ A}$		1.17	1.45	Ω
	$R_{DS(on)2}$	$V_{GS} = -4.0\text{ V}, I_D = -0.2\text{ A}$		1.25	1.55	Ω
	$R_{DS(on)3}$	$V_{GS} = -2.5\text{ V}, I_D = -0.15\text{ A}$		2.25	2.98	Ω
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V}$		29		pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$		15		pF
Reverse Transfer Capacitance	C_{rss}	$f = 1\text{ MHz}$		3.0		pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, I_D = -0.2\text{ A}$		23		ns
Rise Time	t_r	$V_{GS} = -4.0\text{ V}$		39		ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 10\ \Omega$		50		ns
Fall Time	t_f			33		ns
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 0.4\text{ A}, V_{GS} = 0\text{ V}$		0.93		V

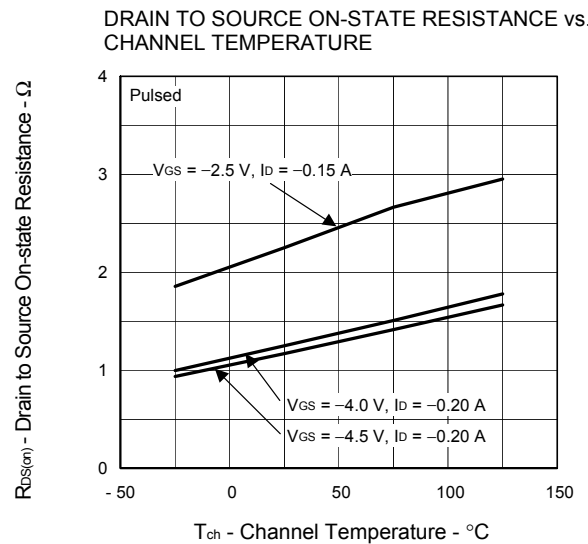
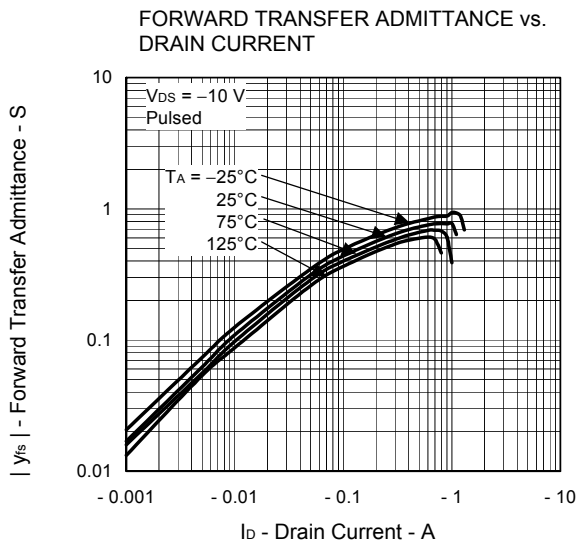
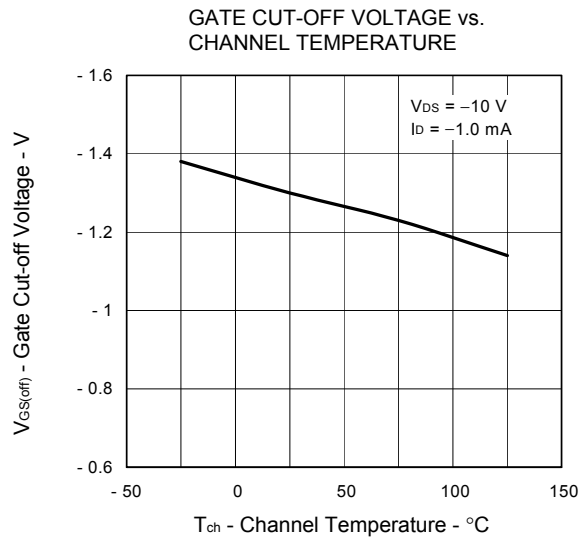
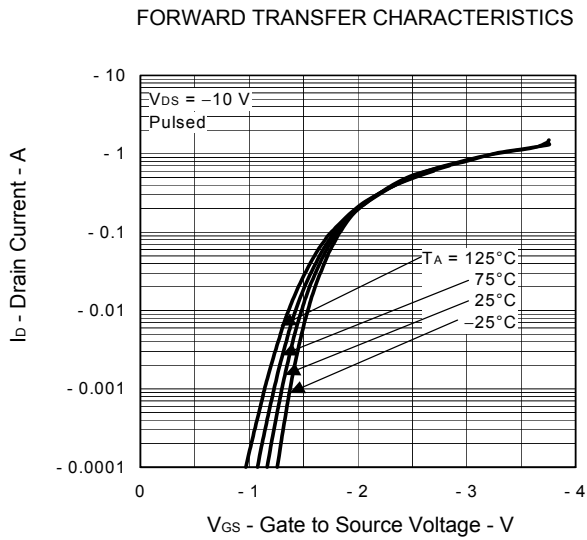
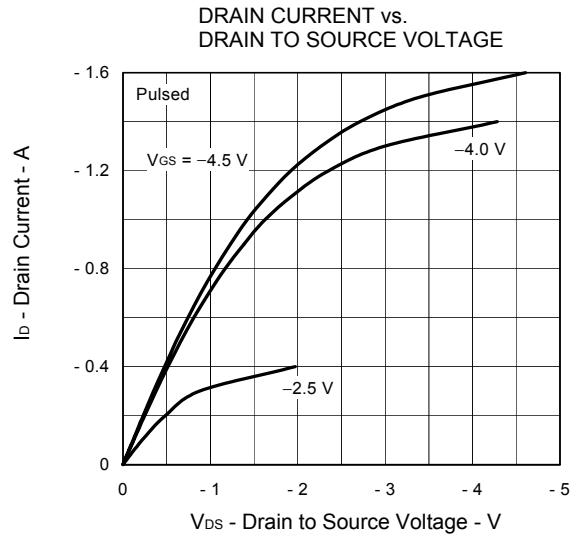
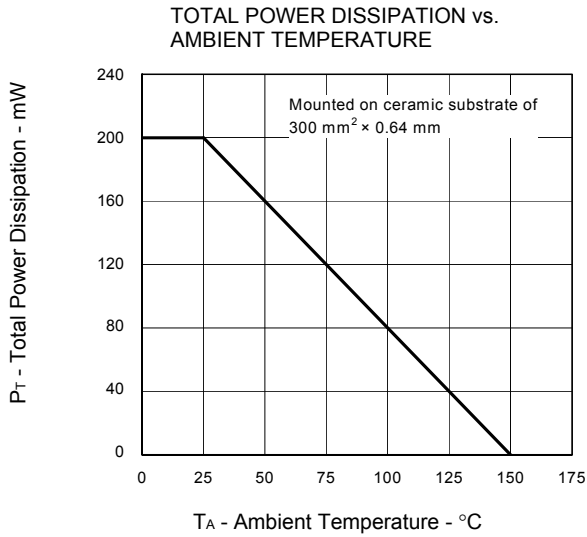
Note Pulsed PW $\leq 350\ \mu\text{s}$, Duty Cycle $\leq 2\%$

TEST CIRCUIT SWITCHING TIME

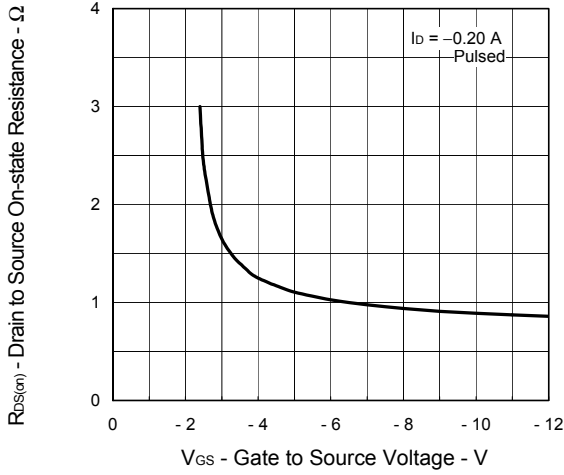


$\tau = 1\ \mu\text{s}$
Duty Cycle $\leq 1\%$

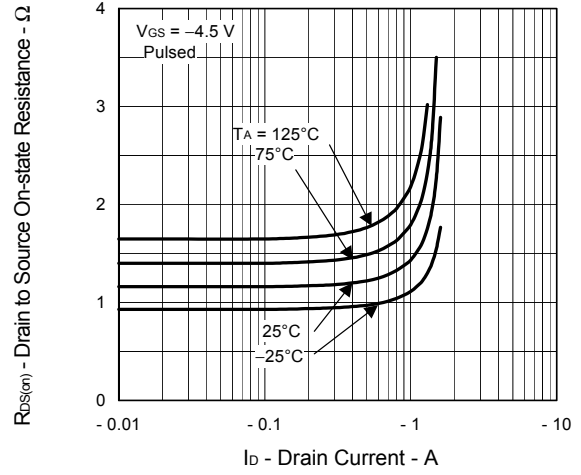
TYPICAL CHARACTERISTICS (T_A = 25°C)



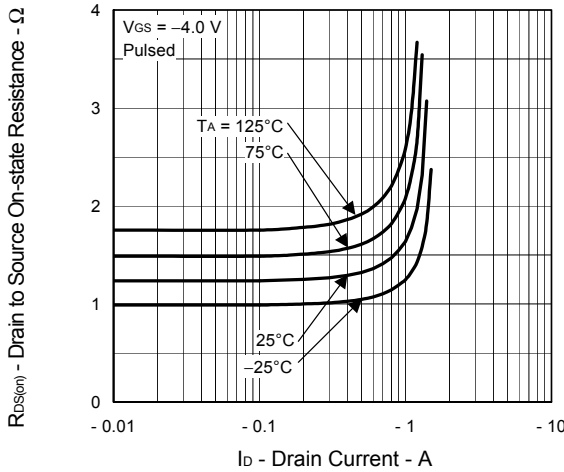
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



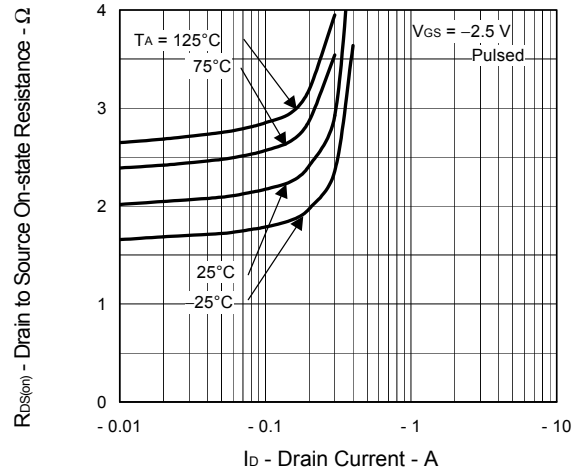
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



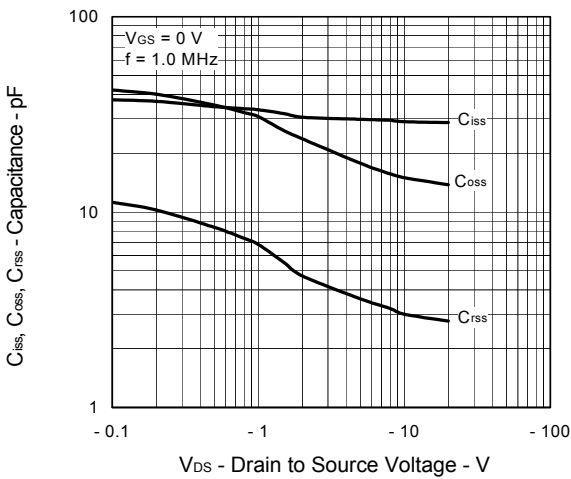
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



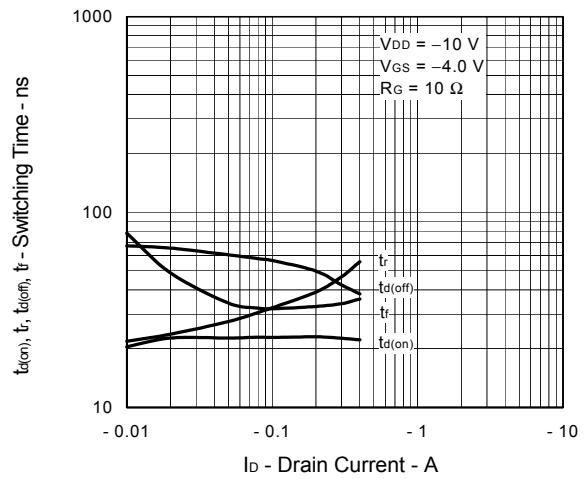
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

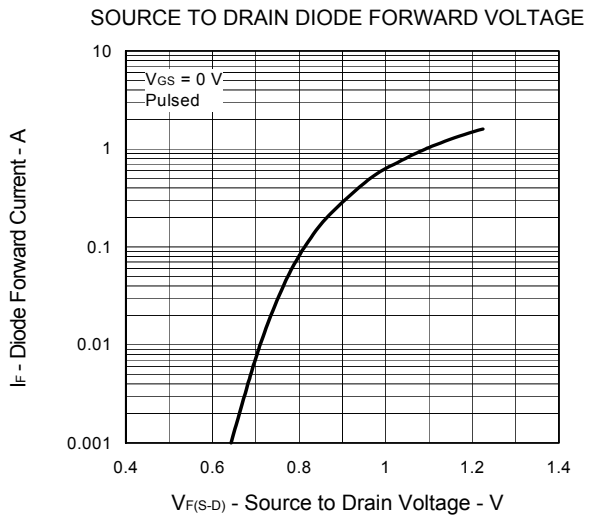


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



SWITCHING CHARACTERISTICS





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